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Kind regards,

Team Nexperia



# **PBSS5130T**

30 V; 1 A PNP low VCEsat (BISS) transistor

9 July 2013

**Product data sheet** 

## 1. General description

PNP low V<sub>CEsat</sub> Breakthrough In Small Signal (BISS) transistor in a small SOT23 Surface-Mounted Device (SMD) plastic package.

### 2. Features and benefits

- Small SMD plastic package
- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability: I<sub>C</sub> and I<sub>CM</sub>
- Higher efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- DC-to-DC conversion
- Supply line switching
- Battery charger
- LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-30	V
I <sub>C</sub>	collector current		-	-	-1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	-	-3	Α
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_C$ = -500 mA; $I_B$ = -50 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	220	mΩ





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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	<u> </u>	C
2	Е	emitter		В—
3	С	collector	1 2	'*_
			TO-236AB (SOT23)	sym132

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5130T	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

## 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PBSS5130T	%3E

[1] % = placeholder for manufacturing site code

30 V; 1 A PNP low VCEsat (BISS) transistor

## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-30	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-30	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-1	Α
I <sub>СМ</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-3	Α
I <sub>BM</sub>	peak base current			-	-300	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			<u>[2]</u>	-	480	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance	in free air	[1]	-	-	417	K/W
	from junction to ambient		[2]	-	-	260	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

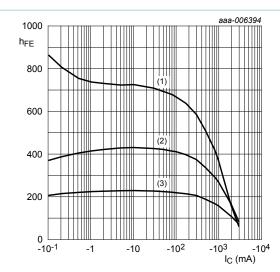
30 V; 1 A PNP low VCEsat (BISS) transistor

## 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = -30 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
	current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -4 \text{ V; } I_{C} = 0 \text{ A; } T_{amb} = 25 ^{\circ}\text{C}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -2 \text{ V; } I_{C} = -100 \text{ mA; pulsed;}$ $t_{p} \le 300 \text{ µs; } \delta \le 0.02 \text{ ; } T_{amb} = 25 \text{ °C}$	300	450	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -500 mA; pulsed; $t_{p} \le 300 \text{ μs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	260	350	-	
		$V_{CE}$ = -2 V; $I_{C}$ = -1 A; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	210	290	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C$ = -100 mA; $I_B$ = -1 mA; pulsed; $t_p \le 300$ μs; $\delta \le 0.02$ ; $T_{amb}$ = 25 °C	-	-	-100	mV
		$I_{C}$ = -1 A; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-	-225	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p} \le 300 \text{ µs}; \delta \le 0.02 ; T_{amb}$ = 25 °C	-	-	220	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_C$ = -2 A; $I_B$ = -200 mA; pulsed; $t_p \le 300 \ \mu s$ ; δ ≤ 0.02 ; $T_{amb}$ = 25 °C	-	-	-1.1	V
$V_{BEon}$	base-emitter turn-on voltage	$V_{CE}$ = -2 V; $I_{C}$ = -100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02 \ ; T_{amb}$ = 25 °C	-	-	-0.75	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = -10 V; $I_{C}$ = -100 mA; f = 100 MHz; $T_{amb}$ = 25 °C	100	200	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB}$ = -10 V; $I_{E}$ = 0 A; $i_{e}$ = 0 A; $f$ = 1 MHz; $f_{amb}$ = 25 °C	-	-	28	pF

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$$V_{CE}$$
 = -2  $V$ 

(1) 
$$T_{amb}$$
 = 150 °C

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55$$
 °C

Fig. 1. DC current gain as a function of collector current; typical values

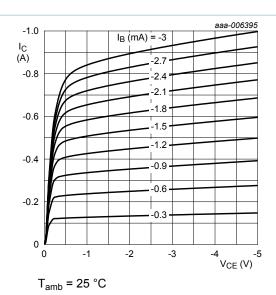
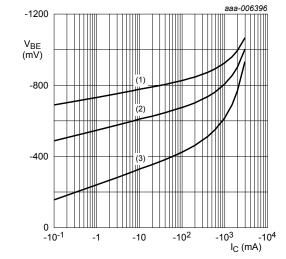


Fig. 2. Collector current as a function of collectoremitter voltage; typical values



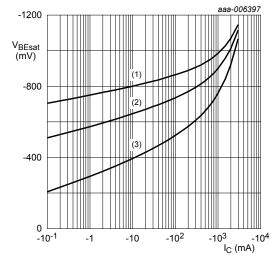
$$V_{CE} = -2 V$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 3. Base-emitter voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 20$$

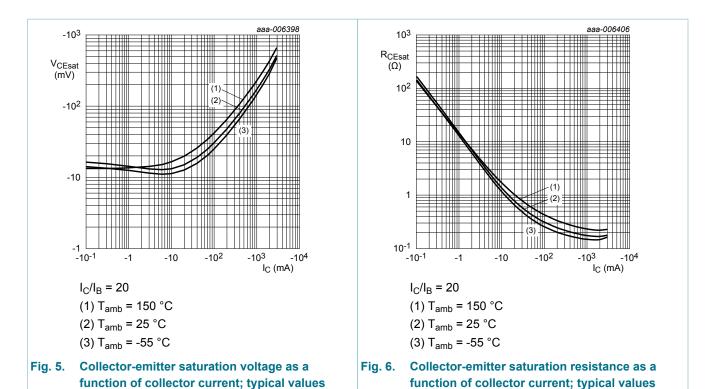
(1) 
$$T_{amb} = -55 \,^{\circ}C$$

(2) 
$$T_{amb}$$
 = 25 °C

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

#### 30 V; 1 A PNP low VCEsat (BISS) transistor

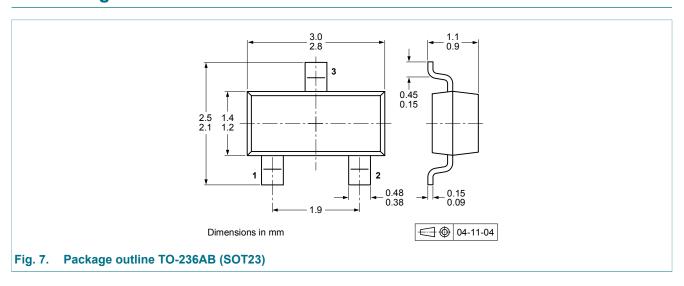


### 11. Test information

#### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

## 12. Package outline



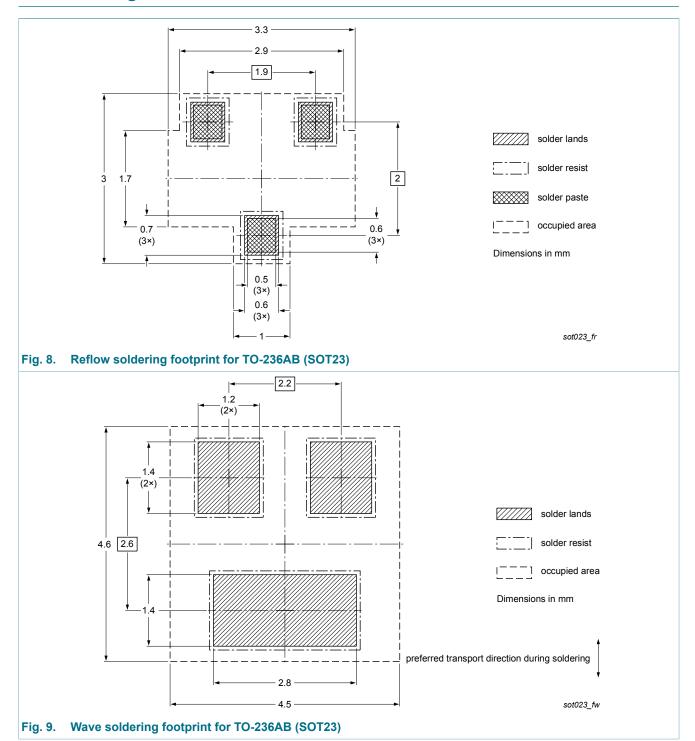
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## 13. Soldering



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## 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS5130T v.2	20130709	Product data sheet	-	PBSS5130T v.1
Modifications:	of NXP Semicondu  Legal texts have be Sections "General e Section "Marking": Table "Limiting value Table "Characterist Figures 1 to 6: adde Section "Test inform	een adapted to the new condescription", "Features and updated ues": ambient temperature ics": base-emitter saturation and the condescription and the condescript	ompany name where app nd benefits" and "Applicat e T <sub>amb</sub> updated ion voltage V <sub>BEsat</sub> added	oropriate. ions": updated
PBSS5130T v.1	20031212	Product data sheet	-	-

#### 30 V; 1 A PNP low VCEsat (BISS) transistor

### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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### 30 V; 1 A PNP low VCEsat (BISS) transistor

### 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	3
10	Characteristics	4
11	Test information	6
11.1	Quality information	6
12	Package outline	6
13	Soldering	7
14	Revision history	8
15	Legal information	9
15.1	Data sheet status	9
15.2	Definitions	9
15.3	Disclaimers	9
15.4	Trademarks	10

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